CEL

RF Low Noise FET
CE3522K2

12GHz Super Low Noise FET in Hollow Plastic PKG

DESCRIPTION

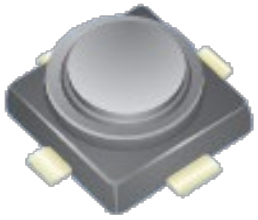
- Super Low Noise and High Gain
- Hollow (Air Cavity) Plastic package

FEATURES

- Super Low noise figure and high associated gain:
  NF = 0.32 dB TYP., Ga = 14.0 dB TYP.
  @VDS=2V, ID=10mA, f=12GHz

PACKAGE

- Micro-X plastic package



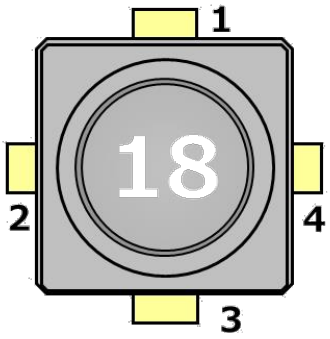
APPLICATIONS

- KU Band LNB (Low Noise Block)
  Suitable for 1st Stage

ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Description
CE3522K2	CE3522K2-C1	Micro-X plastic package	18	• Embossed tape 8 mm wide • Pin 4 (Gate) faces the perforation side of the tape • MOQ 10kpcs/reel

PIN CONFIGURATION AND INTERNAL BLOCK DIAGRAM



Pin No.	Pin Name
1	Source
2	Drain
3	Source
4	Gate

ABSOLUTE MAXIMUM RATINGS

(T_A = +25°C, unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain to Source Voltage	V_{DS}	4.0	V
Gate to Source Voltage	V_{GS}	-3.0	V
Drain Current	I_D	I_{DSS}	mA
Gate Current	I_G	80	μA
Total Power Dissipation	P_{tot}	125	mW
Channel Temperature	T_{ch}	+150	°C
Storage Temperature	T_{stg}	-55 to +125	°C
Operation Temperature	T_{op}	-55 to +125[Note]	°C

Note Refer to Total Power Dissipation vs. Ambient Temperature graph on page 4

RECOMMENDED OPERATING RANGE

(T_A = +25°C, unless otherwise specified)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V_{DS}	+1	+2	+3	V
Drain Current	I_D	5	10	15	mA

ELECTRICAL CHARACTERISTICS

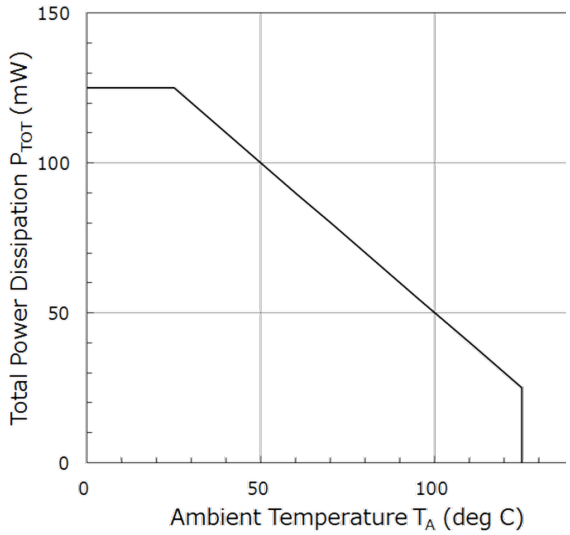
(T_A = +25˚C, unless otherwise specified)

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Gate to Source Leak Current	I_{GSO}	V_{GS} = -3.0V	-	0.4	10	μA
Saturated Drain Current	I_{DSS}	V_{DS} = 2V, V_{GS} = 0V	23	40	57	mA
Gate to Source Cut-off Voltage	$V_{GS\ (off)}$	V_{DS} = 2V, I_D = 100μA	-1.10	-0.75	-0.39	V
Transconductance	Gm	V_{DS} = 2V, I_D = 10mA	47	62	-	mS
Noise Figure	NF	V_{DS} = 2V, I_D = 10mA, f = 12GHz	-	0.32	0.52	dB
Associated Gain	Ga		12.8	14	-	dB

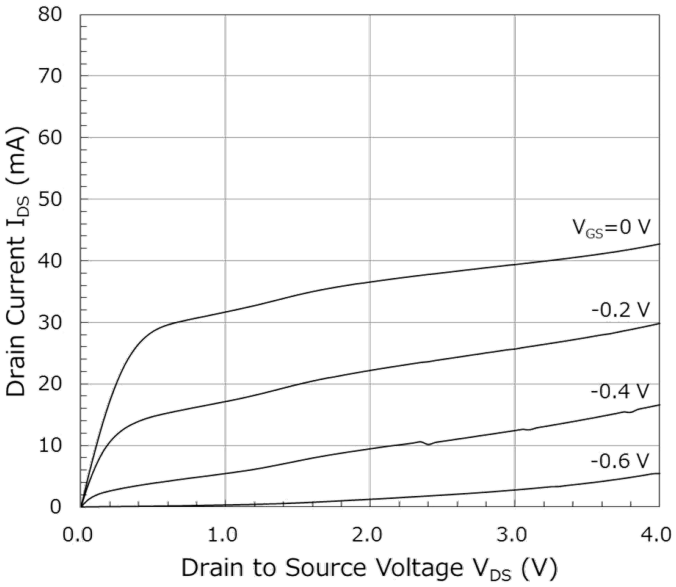
Typical Characteristics:

(TA=+25℃, unless otherwise specified)

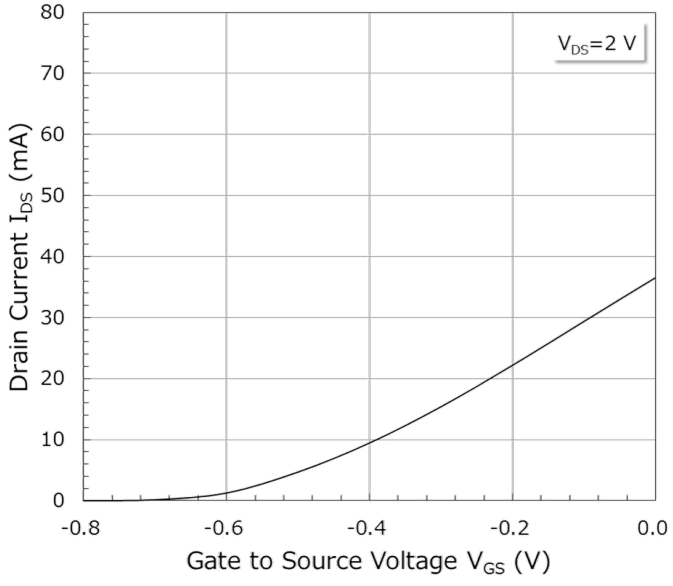
TOTAL POWER DISSIPATION vs. AMBIEN T TEMPERATURE



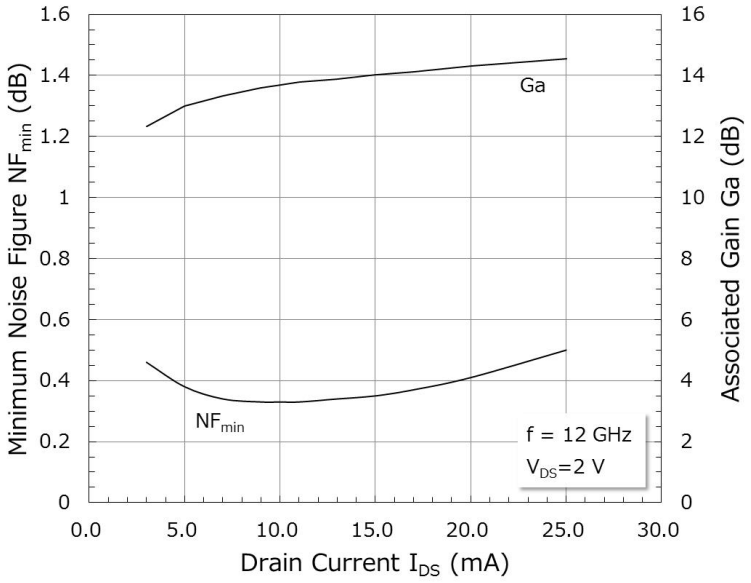
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



DRAIN CURRENT vs. GATE TO SOURCE VOLTAGE



MINIMUM NOISE FIGURE & ASSOCIATED GAIN vs. DRAIN CURRENT



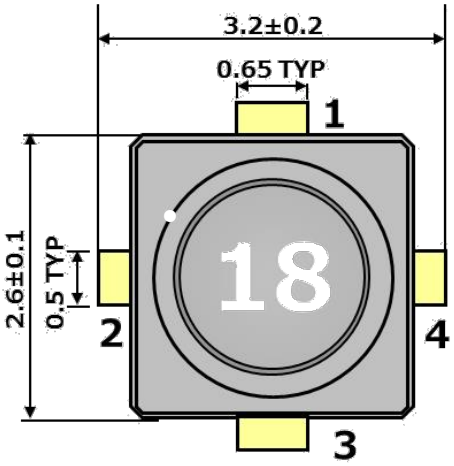
S-PARAMETERS

S-Parameters are available on CEL's Part Summary page under S-parameters

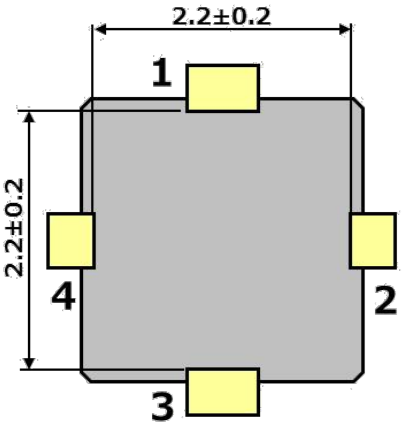
RECOMMENDED SOLDERING CONDITIONS

Recommended Soldering Conditions are available on CEL's Part Summary page under Associated Documents

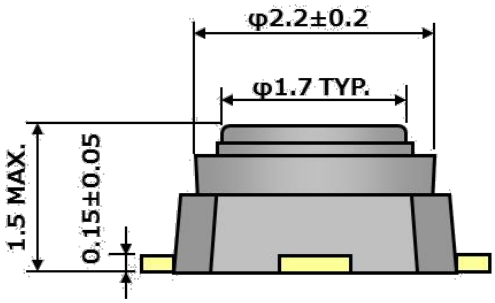
PACKAGE DIMENSIONS:



(Top view)



(Bottom view)



(Side view)

PIN CONNECTIONS

1 : Source 2 : Drain
3 : Source 4 : Gate

Unit [mm]

REVISION HISTORY

Version	Change to current version	Page(s)
CDS-0018-04 (Issue A) January 12,2023	Initial datasheet	N/A

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- Do not dispose in fire or break up this product.
- Do not chemically make gas or powder with this product.
- When discarding this product, please obey the laws of your country.
- Do not lick the product or in any way allow it to enter the mouth.

[CAUTION]

Although this device is designed to be as robust as possible, ESD (Electrostatic Discharge) can damage this device. This device must be protected at all times from ESD. Static charges may easily produce potentials of several kilovolts on the human body or equipment, which can discharge without detection. Industry-standard ESD precautions should be used at all times.

CEL Headquarters • 5201 Great America Parkway, Suite 320 • Santa Clara, CA 95054 • Tel: (408) 919-2500 • www.cel.com

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